

REMARKS

Claims 1-19 are all the claims pending in the application. Claims 1-13 and 17-19 are withdrawn from consideration on the basis of an election made by Applicant without traverse. Claim 16 is allowed. Claim 15 was amended in the previous amendment to place the claim in independent form. The Examiner now has withdrawn the indication that claim 14 is allowable and has stated in a telephone interview on November 13, 2002 that the claim would be allowable if amended to have limitations similar to those in claim 15. Applicant has amended claim 14 to now include limitations from claim 15 that are directed to the making of silicon carbide.

Allowable Subject Matter

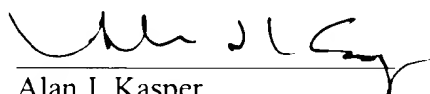
Applicant respectfully submits that claims 14 and 15 have clearly been demonstrated to be allowable on the basis of the novel and unobvious steps that are taken from parent claim 1 and now recited in claims 14 and 15.

Applicant also respectfully submits that, on the basis of the demonstration herein that claim 1 forms the basis for allowability of claim 15, as the prior art does not teach such method, claim 1 also should be allowable. Those claims that depend from claim 1, namely claims 2-13, also should be allowable. Finally, claims 17-19 also should be allowed, as the two distinguishing steps of claim 1 are recited in these claims. No new search or new issues would be involved in reaching a conclusion that all of claims 1-19 should be allowed.

In view of the above, reconsideration and allowance of this application are now believed to be in order, and such actions are hereby solicited.

The USPTO is directed and authorized to charge all required fees, except for the Issue Fee and the Publication Fee, to Deposit Account No. 19-4880. Please also credit any overpayments to said Deposit Account.

Respectfully submitted,



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APPENDIX
VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS:

The claims are amended as follows:

14. (Amended) A silicon carbide having a region which has an impurity concentration gradient between $1 \times 10^{22}/\text{cm}^4$ and $4 \times 10^{24}/\text{cm}^4$ in the thickness direction, said silicon carbide being manufactured by the method comprising:

depositing silicon from a vapor phase or a liquid phase onto a substrate and forming a silicon layer on the substrate;

doping the silicon layer with an impurity composed of at least one element selected from a group consisting of N, B, Al, Ga, In, P, As, Sb, Se, Zn, O, Au, V, Er, Ge, and Fe, to form a doped silicon layer; and

carbonizing the doped silicon layer into a silicon carbide layer of the silicon carbide doped with the impurity.